

Silicon NPN Power Transistors

2SC2611

DESCRIPTION

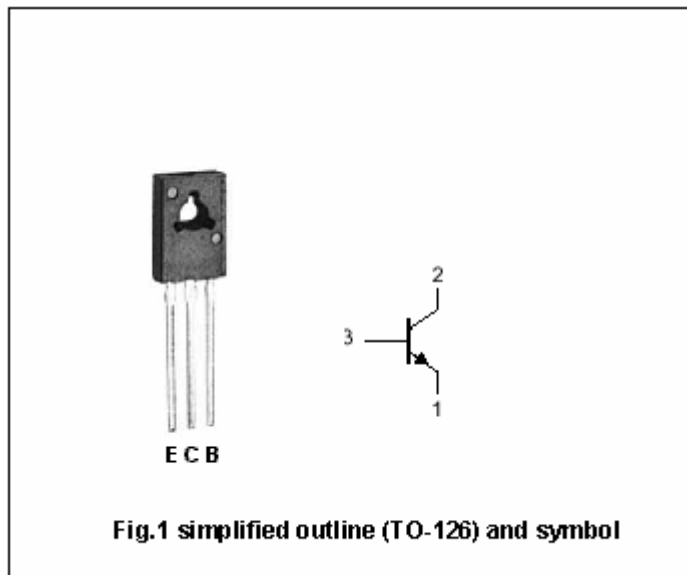
- With TO-126 package
- High breakdown voltage

APPLICATIONS

- For high voltage amplifier TV video output applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

ABSOLUTE MAXIMUM RATINGS($T_c=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		0.1	A
P_C	Collector power dissipation	$T_a=25$	1.25	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=1mA; R_{BE}=\infty$	300			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=10\mu A; I_E=0$	300			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=10\mu A; I_C=0$	5			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C=20mA; I_B=2mA$			1.5	V
I_{CEO}	Collector cut-off current	$V_{CE}=250V; R_{BE}=\infty$			1.0	μA
h_{FE}	DC current gain	$I_C=20mA; V_{CE}=20V$	30		200	
f_T	Transition frequency	$I_C=20mA; V_{CE}=20V$	50	80		MHz
C_{OB}	Collector output capacitance	$I_E=0; V_{CB}=20V; f=1MHz$			4.0	pF

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PACKAGE OUTLINE

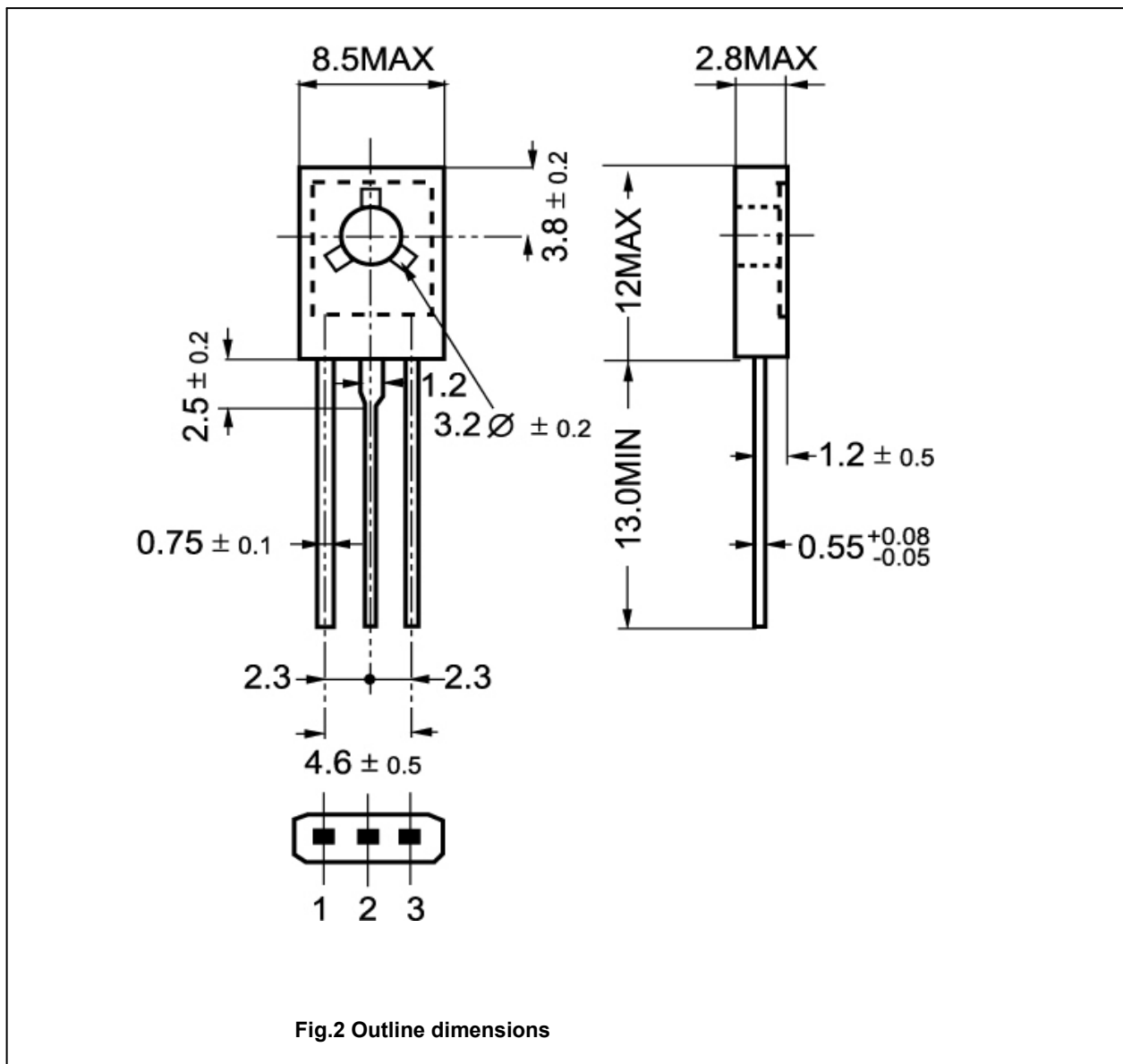


Fig.2 Outline dimensions